L Number	Hits	Search Text	DB	Time stamp
-	1192	<pre>@ad<=20010104 and 'heating substrate' and 'amorphous silicon'</pre>	USPAT; US-PGPUB; EPO; JPO;	2003/04/11 13:46
-	943	((438/486) or (438/482)).CCLs.	DERWENT; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/03
_	71	(((438/486) or (438/482)).CCLS.) and @ad<=20010104 and 'heating substrate' and 'amorphous silicon'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/03 13:00
-	2	(@ad<=20010104 and 'heating substrate' and 'amorphous silicon') and @ad<=20010104 and 'heating substrate' and 'amorphous silicon' and MILC	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/03 13:18
-	2	(((438/486) or (438/482)).CCLS.) and MILC and 'low temperature'	USPĀT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/03 13:36
-	2	(@ad<=20010104 and 'heating substrate' and 'amorphous silicon') and MILC and 'low temperature'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/03 13:06
_	0	@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating' with 'while depositing'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/07 12:01
-	181	@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/03 13:11
_	109	(@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating') and 'depositing'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/03
-	14	@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating' with 'depositing'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/03
-	2	(@ad<=20010104 and 'heating substrate' and 'amorphous silicon') and @ad<=20010104 and 'amorphous silicon' and MILC	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/24
-	303	(((438/486) or (438/482)).CCLS.) and 'low temperature'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/03 13:37
_	52	(((438/486) or (438/482)).CCLS.) and 'low temperature' and 'heating substrate'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/03
-	0	@ad<=20010104 and heating adjl substrate with depositing same metal and MILC	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/24 13:51

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_	58	@ad<=20010104 and MILC	USPAT;	2003/11/07
			US-PGPUB;	11:18
	1		EPO; JPO;	
	}		DERWENT;	}
			IBM_TDB	i
-	0	@ad<=20010104 and heating adjl substrate	USPAT;	2002/10/24
		adj1 while same 'depositing metal'	US-PGPUB;	13:54
	Ì		EPO; JPO;	ì
			DERWENT;	
_		@ad<=20010104 and heat adj1 substrate	IBM_TDB	2002/10/24
		adjl while same 'depositing metal'	USPAT; US-PGPUB;	13:54
	}	adji wiiile same depositing metal	EPO; JPO;	13.54
			DERWENT;	
			IBM TDB	
_	3	@ad<=20010104 and heat adj1 substrate	USPAT;	2002/10/24
		same 'depositing metal'	US-PGPUB;	13:56
	ļ		EPO; JPO;	
			DERWENT;	1
	1		IBM_TDB	Į. Į
-	74	(- · · · · · · · · · · · · · · · · · ·	USPAT;	2002/10/24
	ļ	same 'depositing metal'	US-PGPUB;	14:15
			EPO; JPO;	
			DERWENT;	\
	1.5	0-14 20010104 1 11-4 111-4 1	IBM_TDB	2002/10/24
_	15	@ad<=20010104 and 'hot metallization'	USPAT; US-PGPUB;	2002/10/24 14:16
			EPO; JPO;	14:16
	1		DERWENT;	ļ
			IBM TDB	i
_	191	@ad<=20010104 and 'amorphous silicon'	USPAT;	2002/10/24
		same 'heating substrate'	US-PGPUB;	15:55
	1	bame neading babberate	EPO; JPO;	20.00
			DERWENT;	
	1		IBM TDB	
-	12		USPAT;	2002/10/24
	1	same 'heating substrate' same 'metal'	US-PGPUB;	15:40
			EPO; JPO;	
			DERWENT;	1
			IBM_TDB	
-	3778	'	USPAT;	2002/10/24
		(438/334) or (257/57)).CCLS.	US-PGPUB;	15:42
			EPO; JPO;	i
	ŀ		DERWENT;	
_	5.4	(((438/149) or (438/158) or (438/315) or	IBM_TDB USPAT;	2002/10/24
	34	(((438/149) or (438/138) or (438/315) or (438/334) or (257/57)).CCLS.) and	US-PGPUB;	15:56
		(436/334) 01 (237/37)).CCLS.) and (436/334) 01 (237/37)).CCLS.) and (436/334) 01 (237/37)).CCLS.)	EPO; JPO;	10.00
		dan boototo and medering subscrace	DERWENT;	
			IBM TDB	1
_	2	"20020137310"	USPAT;	2003/11/07
			US-PGPUB;	11:55
			EPO; JPO;	1
			DERWENT;	
	1		IBM_TDB	
-	447	1 -	USPAT;	2003/04/11
		crystallization	US-PGPUB;	14:35
			EPO; JPO;	
			DERWENT;	
	27222	((112571) (114201))	IBM_TDB	1 2007 (04 /33
-	318928	(("257") or ("438")).CLAS.	USPAT;	2003/04/11
			US-PGPUB; EPO; JPO;	13:59
			DERWENT;	}
			IBM TDB	1
	124	(@ad<=20010104 and low adj temperature	USPAT;	2003/04/11
_		I (caa, boolotor and fow adj cemperacule	OPTET!	2000/03/11
-	124		US-PGPUB:	114:13
-	124	adj crystallization) and 'nickel'	US-PGPUB; EPO; JPO;	14:13
-	124		US-PGPUB; EPO; JPO; DERWENT;	14:13

	1	("6524662").PN.	VICD NO.	1 2002 /04 /11
_	1	(~6524662~).PN.	USPAT;	2003/04/11
			US-PGPUB;	14:07
			EPO; JPO; DERWENT;	
			IBM TDB	
_	28	(@ad<=20010104 and low adj temperature	USPAT;	2003/04/11
	20	adj crystallization) and heat adj	US-PGPUB;	14:14
		substrate and 'nickel'	EPO; JPO;	1 1 1 1 1
			DERWENT;	
	11		IBM TDB	
_	9	@ad<=20010104 and deposit adj nickel same	USPAT;	2003/04/11
		'heat' same 'substrate'	US-PGPUB;	14:39
			EPO; JPO;	
•			DERWENT;	
			IBM TDB	
-	6	1	USPAT;	2003/04/11
	['substrate' same deposit adj nickel	US-PGPUB;	14:40
	ļ		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	62	@ad<=20010104 and MILC	USPAT;	2003/11/07
			US-PGPUB;	11:26
			EPO; JPO;	
			DERWENT;	
		(#6504660#) 777	IBM_TDB	0000 (11 (07
_	3	("6524662").PN.	USPAT;	2003/11/07
			US-PGPUB;	11:22
	ļ .		EPO; JPO;	
			DERWENT;	
	24	Gad <-20010104 and Tax according	IBM_TDB	2002/11/07
_	24	Gad<=20010104 and Joo-seung.in.	USPAT; US-PGPUB;	2003/11/07
			EPO; JPO;	11:27
			DERWENT;	
			IBM TDB	
_	39	Joo-seung-ki.in.	USPAT;	2003/11/07
		Soo Beang Mi.in.	US-PGPUB;	11:27
			EPO; JPO;	12127
	,		DERWENT;	
			IBM TDB	
_	2	("6097037").PN.	USPAT;	2003/11/07
			US-PGPUB;	11:57
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	1
-	231		USPAT;	2003/11/07
,	1	same 'nickel' same 'sputtering'	US-PGPUB;	12:02
			EPO; JPO;	
			DERWENT;	
1		A-de 20010104 - 3 t	IBM_TDB	2002/11/05
-	53	@ad<=20010104 and 'amorphous silicon'	USPAT;	2003/11/07
		with 'nickel' with 'sputtering'	US-PGPUB;	12:19
			EPO; JPO;	
			DERWENT;	
_	8	@ad<=20010104 and 'amorphous silicon'	IBM_TDB	2003/11/07
	8	with 'nickel' with 'sputtering' with	USPAT;	2003/11/07
		temperature'	US-PGPUB; EPO; JPO;	12.22
		comperators	DERWENT;	
	1		IBM TDB	
_	222	<pre>@ad<=20010104 and 'sputtering' with</pre>	USPAT;	2003/11/07
	222	'temperature' same 'nickel'	US-PGPUB;	12:22
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	100	@ad<=20010104 and 'sputtering' with	USPAT;	2003/11/07
		'temperature' with 'nickel'	US-PGPUB;	12:27
	Ì	-	EPO; JPO;	
			DERWENT;	

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[
1 1	5	@ad<=20010104 and 'nickel' with	USPAT;	2003/11/07
1		'sputtering temperature'	US-PGPUB;	12:49
[EPO; JPO;	
1			DERWENT;	1
			IBM_TDB	
-	0	@ad<=20010104 and 'nickel' with	USPAT;	2003/11/07
		'oxidation' adjl 'stable' with 'silicide'	US-PGPUB;	12:48
1			EPO; JPO;	1
i			DERWENT;	
			IBM_TDB	1
-	6	@ad<=20010104 and 'nickel' with	USPAT;	2003/11/07
		'oxidation' adj1 'stable'	US-PGPUB;	12:48
			EPO; JPO;	
			DERWENT;	1
ı			IBM_TDB	
-	11	@ad<=20010104 and 'nickel' same	USPAT;	2003/11/07
		'sputtering temperature'	US-PGPUB;	12:55
			EPO; JPO;	(
			DERWENT;	
			IBM TDB	Į .
-	93	@ad<=20010104 and 'nickel' same	USPAT;	2003/11/07
		'oxidation temperature'	US-PGPUB;	12:56
			EPO; JPO;	
			DERWENT;	Į l
			IBM TDB	
-	31	@ad<=20010104 and 'nickel' with	USPAT;	2003/11/07
		'oxidation temperature'	US-PGPUB;	13:02
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	72	@ad<=20010104 and 'nickel' with	USPAT;	2003/11/07
		'silicidation'	US-PGPUB;	13:02
]			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	27	@ad<=20010104 and 'nickel' adj1	USPAT;	2003/11/07
1		'silicidation'	US-PGPUB;	13:04
			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	26	@ad<=20010104 and 'nickel' adj1	USPAT;	2003/11/07
		'silicidation' and 'temperature'	US-PGPUB;	13:04
] 1			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	17	@ad<=20010104 and 'nickel' adj1	USPAT;	2003/11/07
1	Ì	'silicidation' same 'temperature'	US-PGPUB;	13:15
			EPO; JPO;	1
1	١		DERWENT;	1
	j		IBM_TDB	
-	153	<pre>@ad<=20010104 and 'nickel' same 'silicon'</pre>	USPAT;	2003/11/07
		with 'crystallized' same 'temperature'	US-PGPUB;	13:16
1	\		EPO; JPO;	1
			DERWENT;	
	ļ		IBM_TDB	
-	64	<pre>@ad<=20010104 and 'nickel' same 'silicon'</pre>	USPAT;	2003/11/07
	ļ	with 'crystallized' with 'temperature'	US-PGPUB;	13:16
	ļ		EPO; JPO;	
	ļ		DERWENT;	
]			IBM_TDB	
-	2	("5614291").PN.	USPAT;	2003/11/07
			US-PGPUB;	13:22
	ł		EPO; JPO;	
]			DERWENT;	
1			IBM TDB	1